

Docket No. 220212US2/sdc



#2  
6-20-2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Kazuya OHUCHI

SERIAL NO: 10/084,221

GAU: 2815

FILED: February 28, 2002

EXAMINER:

FOR: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

INFORMATION DISCLOSURE/RELATED CASE STATEMENT UNDER 37 CFR 1.97

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☒ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

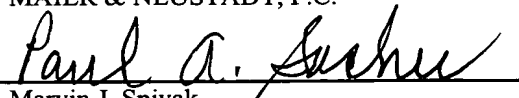
- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

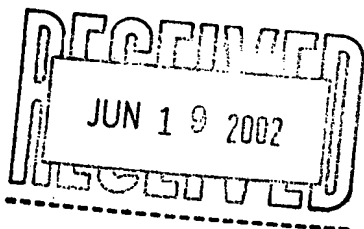
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DOCKET NO: 220212US

Sheet 1 of 1

SERIAL NO: 10/084,221

Group Art Unit: 2815

STATEMENT OF RELEVANCY

**Reference AW on Form 1449:**

This reference discloses electrical property of heavily doped polycrystalline silicon-germanium films were studied. Boron activation is enhanced by increasing germanium fraction. Phosphorous activation also increases with germanium fraction up to 0.35, but in the region over 0.35 germanium fraction, it decreases with increasing germanium fraction.

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### LIST OF RELATED CASES

<u>Docket Number</u>	<u>Serial or Patent No.</u>	<u>Filing or Issue Date</u>	<u>Status or Patentee</u>
PER CLIENT	10/082,257	UNKNOWN	UNKNOWN
PER CLIENT	09/440,928	UNKNOWN	UNKNOWN
220212US2*	10/084,221	02/28/02	PENDING

\*Present application; listed for information  
GJM/sb

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